

PMZB350UPE

20 V, single P-channel Trench MOSFET

1 August 2012

Product data sheet

1. Product profile

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- 1.8 kV ESD protected

1.3 Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_J = 25\text{ }^{\circ}\text{C}$	-	-	-20	V
V_{GS}	gate-source voltage		-8	-	8	V
I_D	drain current	$V_{GS} = -4.5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}; t \leq 5\text{ s}$	[1]	-	-1.4	A
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = -4.5\text{ V}; I_D = -0.3\text{ A}; T_J = 25\text{ }^{\circ}\text{C}$	-	330	450	m Ω

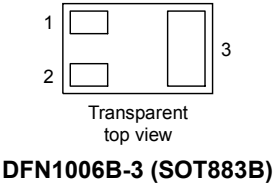
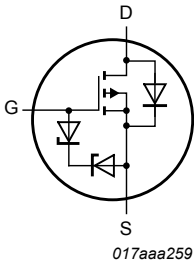
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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2. Pinning information

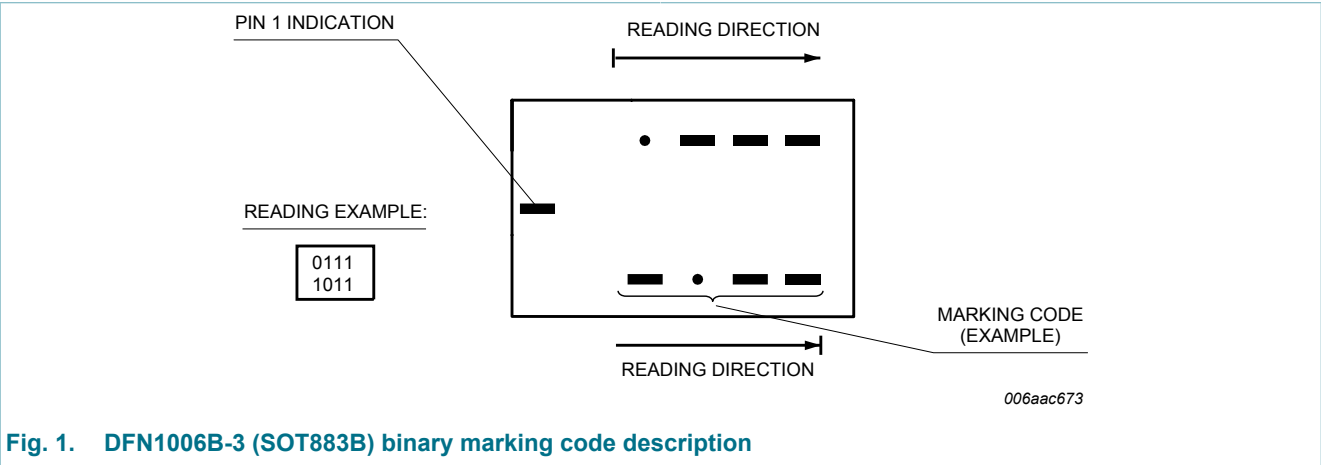
Table 2. Pinning information				
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	S	source		
3	D	drain		

3. Ordering information

Table 3. Ordering information			
Type number	Package		
	Name	Description	Version
PMZB350UPE	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

4. Marking

Table 4. Marking codes	
Type number	Marking code
PMZB350UPE	0100 1100



5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ }^{\circ}\text{C}$		-	-20	V
V_{GS}	gate-source voltage			-8	8	V
I_D	drain current	$V_{GS} = -4.5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}; t \leq 5\text{ s}$	[1]	-	-1.4	A
		$V_{GS} = -4.5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$	[1]	-	-1	A
		$V_{GS} = -4.5\text{ V}; T_{amb} = 100\text{ }^{\circ}\text{C}$	[1]	-	-0.7	A
I_{DM}	peak drain current	$T_{amb} = 25\text{ }^{\circ}\text{C}; \text{single pulse}; t_p \leq 10\text{ }\mu\text{s}$		-	-2.8	A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ }^{\circ}\text{C}$	[2]	-	360	mW
			[1]	-	715	mW
		$T_{sp} = 25\text{ }^{\circ}\text{C}$		-	3125	mW
T_j	junction temperature			-55	150	$^{\circ}\text{C}$
T_{amb}	ambient temperature			-55	150	$^{\circ}\text{C}$
T_{stg}	storage temperature			-65	150	$^{\circ}\text{C}$
Source-drain diode						
I_S	source current	$T_{amb} = 25\text{ }^{\circ}\text{C}$	[1]	-	-0.8	A
ESD maximum rating						
V_{ESD}	electrostatic discharge voltage	HBM	[3]	-	1800	V

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm^2 .

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.

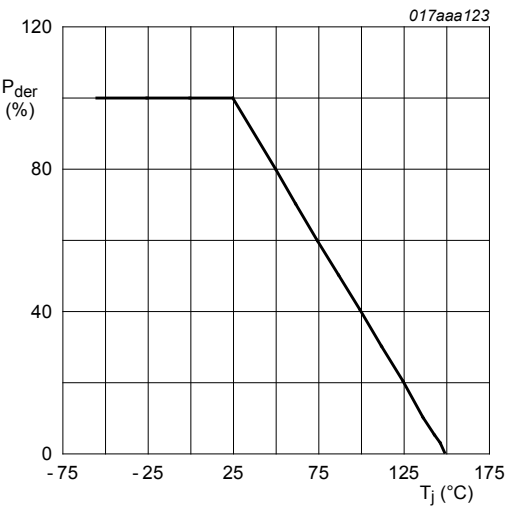


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \%$$

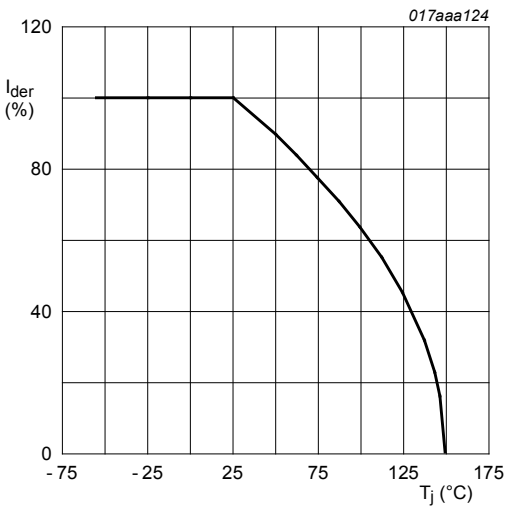


Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

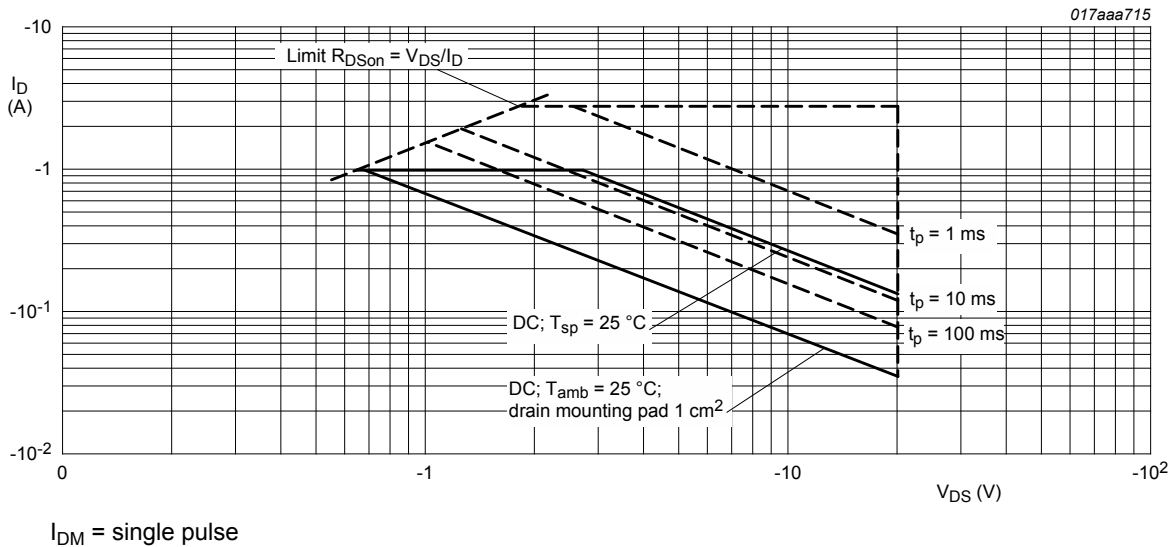


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	304	350	K/W
			[2]	-	150	175	K/W
			[3]	-	90	103	K/W

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	35	40	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm², t ≤ 5 s.

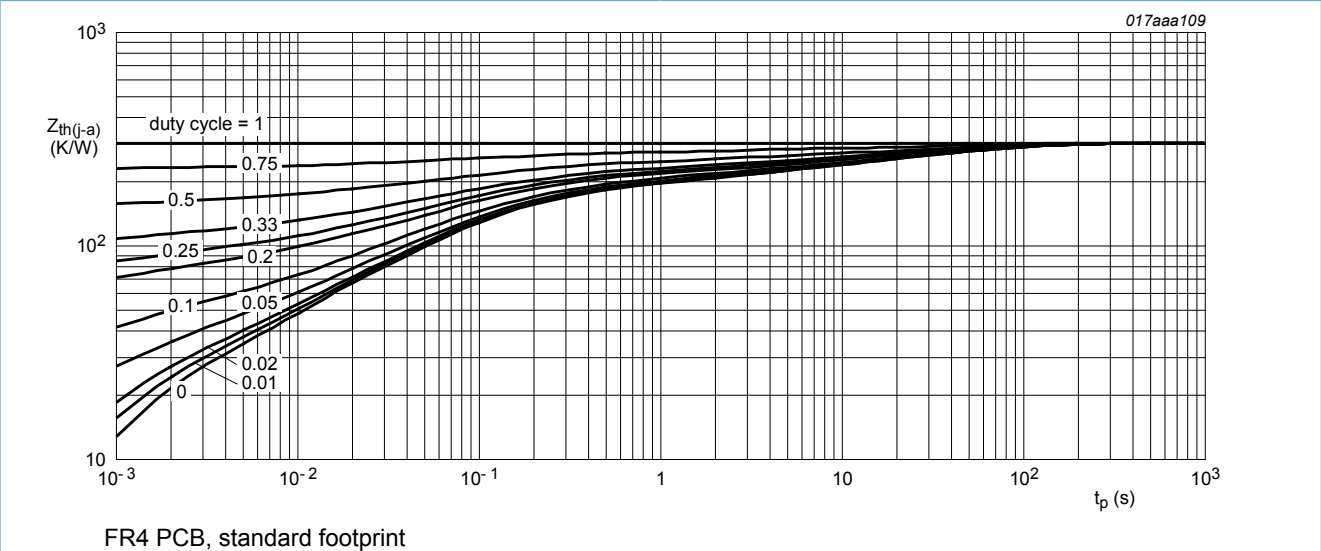


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

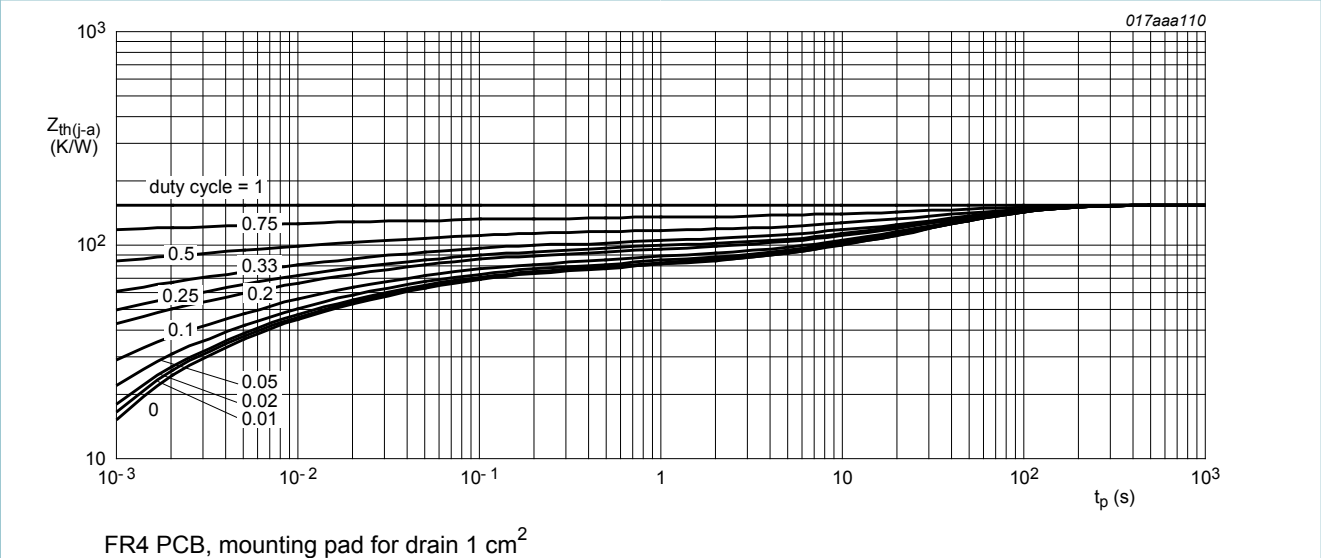


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
V _{(BR)DSS}	drain-source breakdown voltage	I _D = -250 μA; V _{GS} = 0 V; T _j = 25 °C		-20	-	-	V
V _{GSth}	gate-source threshold voltage	I _D = -250 μA; V _{DS} = V _{GS} ; T _j = 25 °C		-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C		-	-	-1	μA
		V _{DS} = -20 V; V _{GS} = 0 V; T _j = 150 °C		-	-	-10	μA
I _{GSS}	gate leakage current	V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C		-	-	-10	μA
		V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C		-	-	10	μA
R _{DSon}	drain-source on-state resistance	V _{GS} = -4.5 V; I _D = -0.3 A; T _j = 25 °C		-	330	450	mΩ
		V _{GS} = -4.5 V; I _D = -0.3 A; T _j = 150 °C		-	478	645	mΩ
		V _{GS} = -2.5 V; I _D = -0.2 A; T _j = 25 °C		-	420	645	mΩ
		V _{GS} = -1.8 V; I _D = -0.1 A; T _j = 25 °C		-	520	940	mΩ
g _{fs}	forward transconductance	V _{DS} = -10 V; I _D = -0.3 A; T _j = 25 °C		-	1.4	-	S
Dynamic characteristics							
Q _{G(tot)}	total gate charge	V _{DS} = -10 V; I _D = -0.3 A; V _{GS} = -4.5 V; T _j = 25 °C		-	1.3	1.9	nC
Q _{GS}	gate-source charge			-	0.2	-	nC
Q _{GD}	gate-drain charge			-	0.25	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V; T _j = 25 °C		-	127	-	pF
C _{oss}	output capacitance			-	34	-	pF
C _{rss}	reverse transfer capacitance			-	25	-	pF
t _{d(on)}	turn-on delay time		V _{DS} = -10 V; I _D = -0.3 A; V _{GS} = -4.5 V; R _{G(ext)} = 6 Ω; T _j = 25 °C		-	4	-
t _r	rise time			-	5	-	ns
t _{d(off)}	turn-off delay time			-	26	-	ns
t _f	fall time			-	9	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I _S = -0.1 A; V _{GS} = 0 V; T _j = 25 °C		-	-0.7	-1.2	V

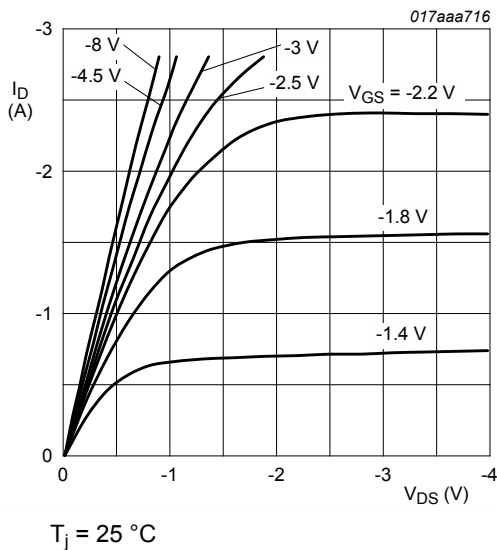


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

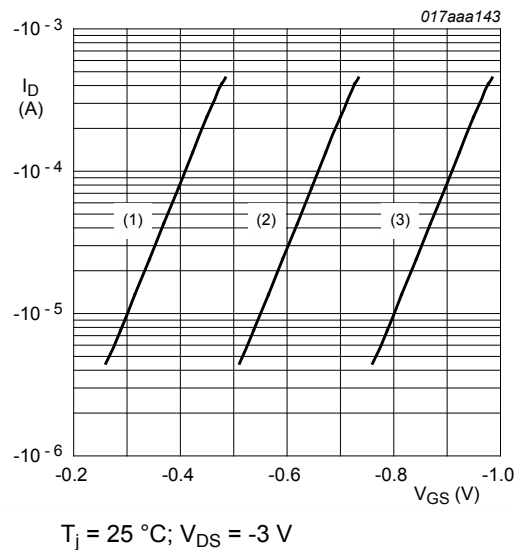


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

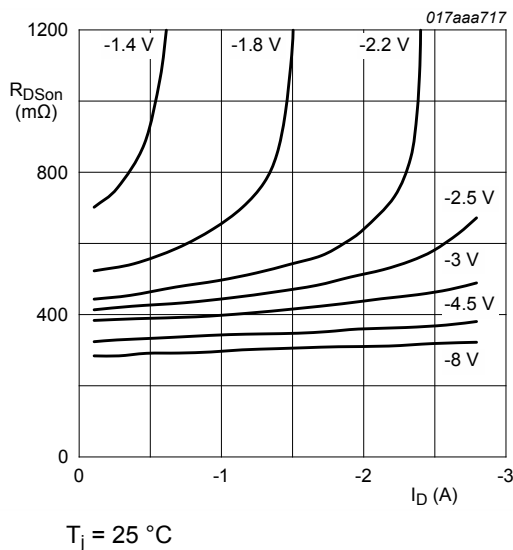


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

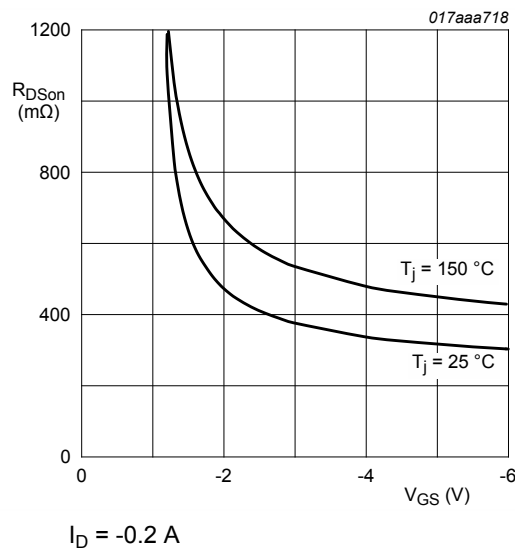


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

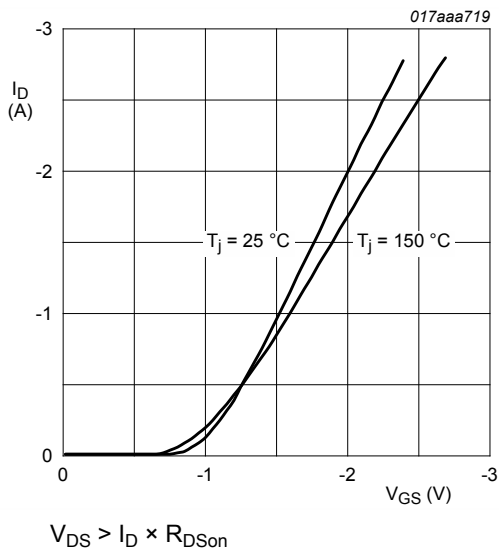


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

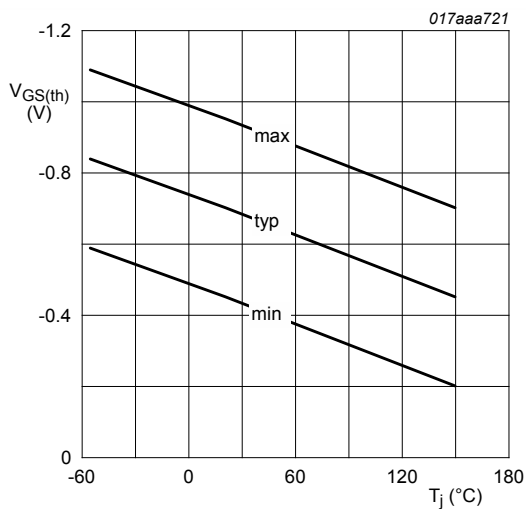


Fig. 13. Gate-source threshold voltage as a function of junction temperature

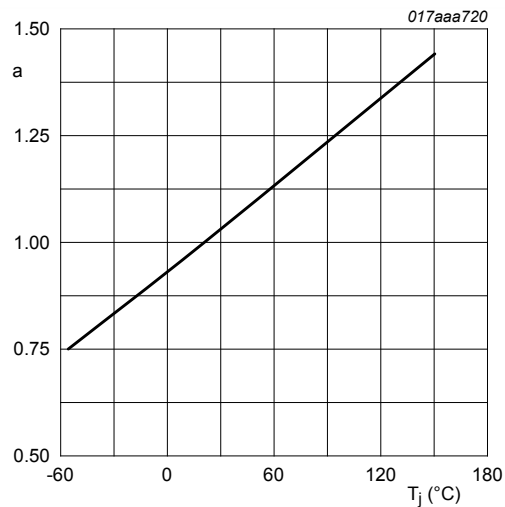


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25\text{ °C})}}$$

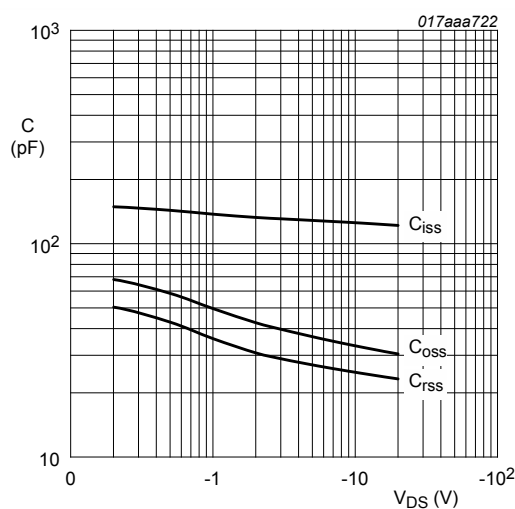


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

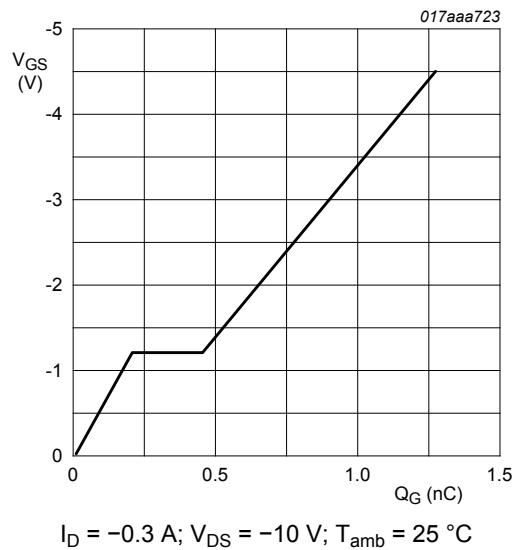


Fig. 15. Gate-source voltage as a function of gate charge; typical values

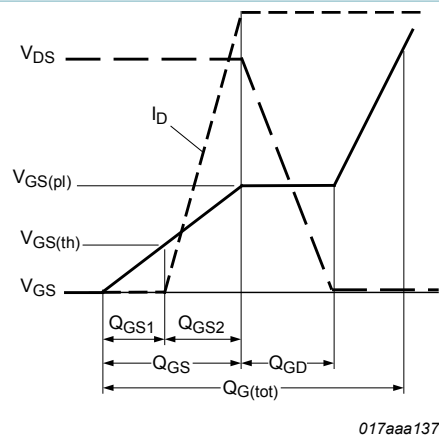


Fig. 16. Gate charge waveform definitions

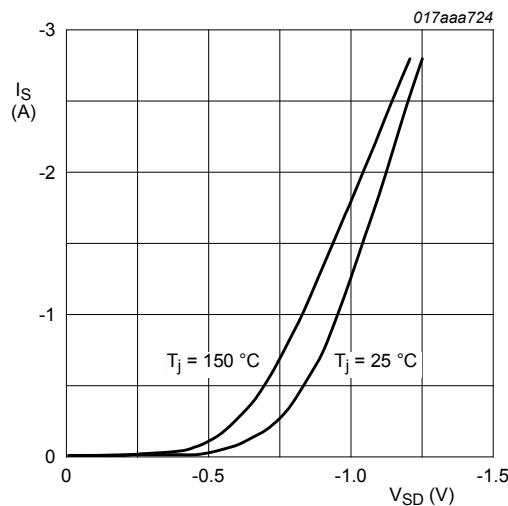


Fig. 17. Source current as a function of source-drain voltage; typical values

8. Test information

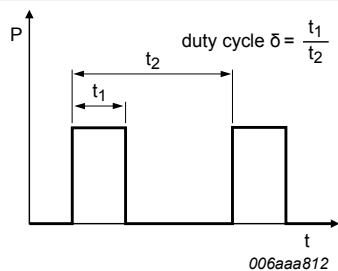
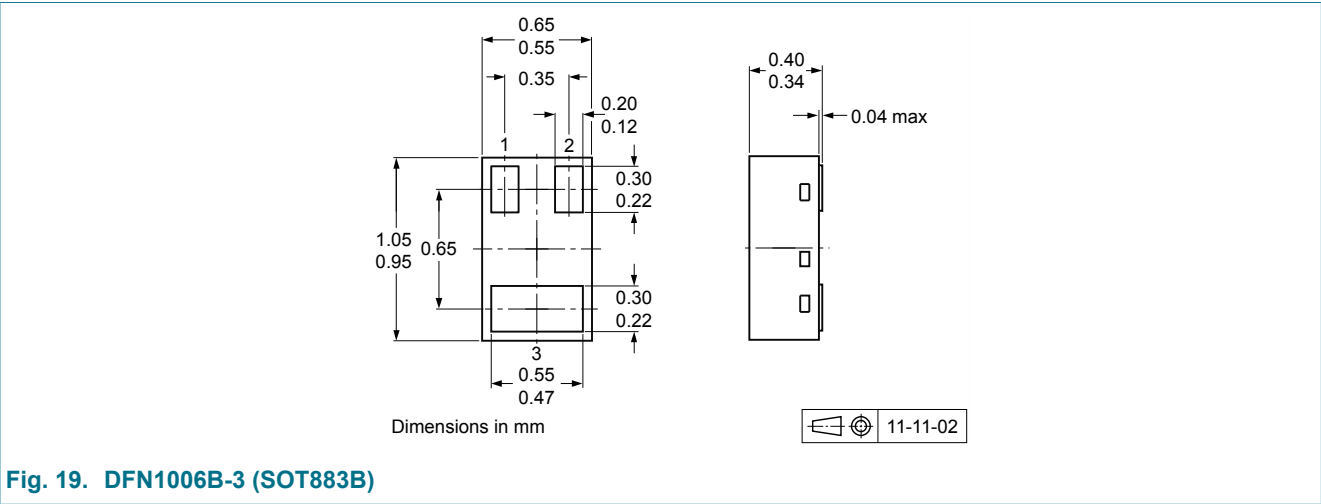


Fig. 18. Duty cycle definition

9. Package outline



10. Soldering

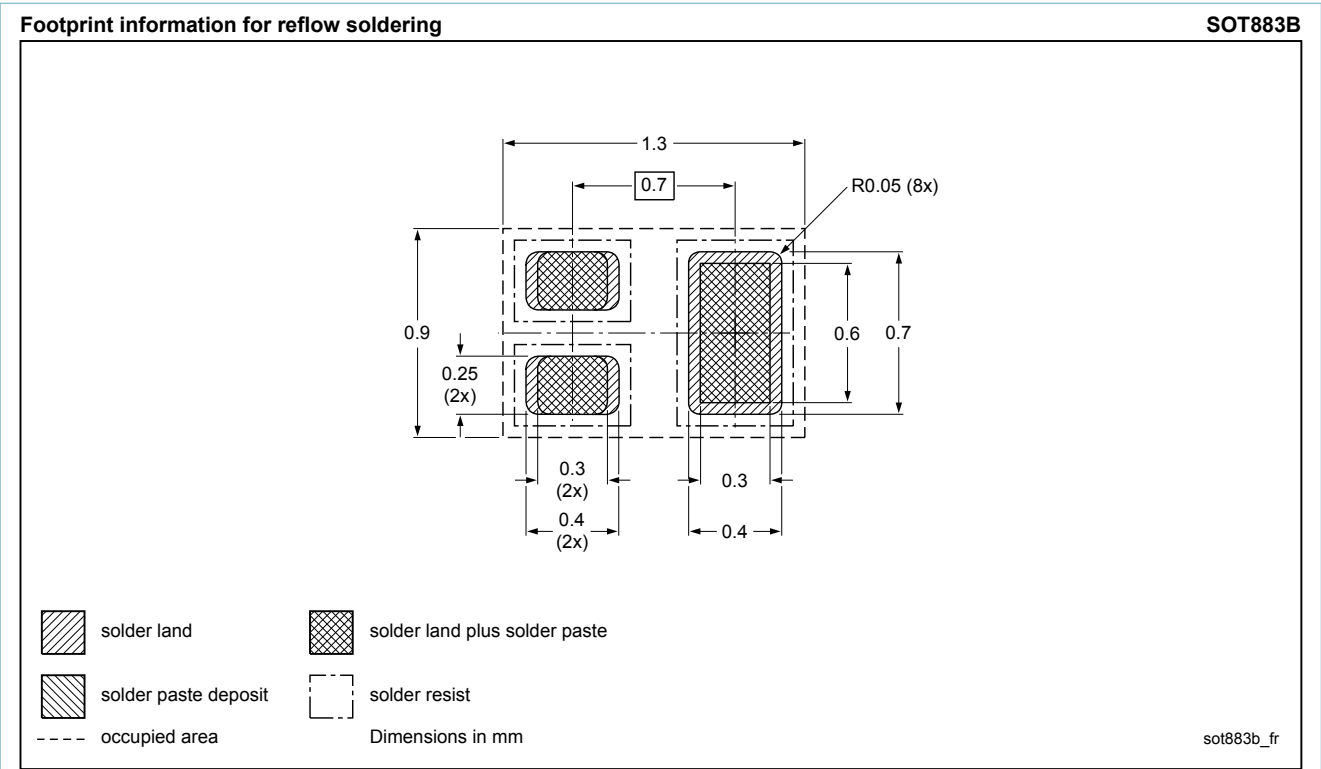


Fig. 20. Reflow soldering footprint for SOT883B (DFN1006B-3)

11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZB350UPE v.1	20120801	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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